

### 1.1 Scope.

This specification covers the detail requirements for a monolithic 10-bit CMOS multiplying digital-to-analog converter.

### 1.2 Part Number.

The complete part number per Table 1 of this specification is as follows:

<b>Device</b>	<b>Part Number<sup>1</sup></b>
-1	AD7533S(X)/883B
-2	AD7533T(X)/883B
-3	AD7533U(X)/883B

**NOTE**

<sup>1</sup>See paragraph 1.2.3 for package identifier.

### 1.2.3 Case Outline.

See Appendix 1 of General Specification ADI-M-1000: package outline:

<b>(X)</b>	<b>Package</b>	<b>Description</b>
Q	Q-16	16-Pin Cerdip
E	E-20A	20-Contact LCC

### 1.3 Absolute Maximum Ratings. ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

$V_{DD}$ to GND . . . . .	−0.3V, +17V
$R_{FB}$ to GND . . . . .	±25V
$V_{REF}$ to GND . . . . .	±25V
Digital Input Voltage Range . . . . .	−0.3V to $V_{DD}$
Output Voltage (Pin 1, Pin 2) . . . . .	−0.3V to $V_{DD}$
Power Dissipation	
Up to $+50^\circ\text{C}$ . . . . .	1000mW
Derates above $+50^\circ\text{C}$ . . . . .	10mW/ $^\circ\text{C}$
Operating Temperature Range . . . . .	−55°C to +125°C
Storage Temperature Range . . . . .	−65°C to +150°C

Note: "Pin numbers refer to DIP package ONLY"

### 1.5 Thermal Characteristics.

Thermal Resistance  $\theta_{JC} = 35^\circ\text{C/W}$  for Q-16 and E-20A  
 $\theta_{JA} = 120^\circ\text{C/W}$  for Q-16 and E-20A

# AD7533—SPECIFICATIONS

Table 1.

Test	Symbol	Device	Design Limit $T_{min}-T_{max}$	Sub Group 1	Sub Group 2, 3	Sub Group 4	Test Condition <sup>1</sup>	Units
Resolution	RES	- 1, 2, 3	10					Bits
Relative Accuracy	RA	- 1	2	2	2			$\pm$ LSB max
		- 2	1	2	1	1		
		- 3	1/2	2	1/2	1/2		
Gain Error <sup>2</sup>	AE	- 1, 2, 3	15	14	15			$\pm$ LSB max
Gain Tempco	TC <sub>AE</sub>	- 1, 2, 3	10					$\pm$ ppm/ $^{\circ}$ C max
Power Supply Rejection	PSRR	- 1, 2, 3	0.008	0.005	0.008		Digital Inputs = V <sub>IH</sub> ; V <sub>DD</sub> = 14V to + 17V	$\pm$ %/% max
Output Leakage Current I <sub>OUT1</sub> (Pin 1)	I <sub>OL</sub>	- 1, 2, 3	200	50	200		Digital Inputs = V <sub>IL</sub> ; (V <sub>REF</sub> = + 10V)	$\pm$ nA max
I <sub>OUT2</sub> (Pin 2)	I <sub>OL</sub>	- 1, 2, 3	200	50	200		Digital Inputs = V <sub>IH</sub> ; (V <sub>REF</sub> = + 10V)	$\pm$ nA max
Output Current Settling Time t <sub>SI</sub>	t <sub>SI</sub>	- 1, 2, 3	800				To $\pm$ 1/2LSB; R <sub>OUT1</sub> = 100 $\Omega$ ; C <sub>OUT1</sub> = 13pF; Digital Inputs = V <sub>IH</sub> to V <sub>IL</sub> or V <sub>IL</sub> to V <sub>IH</sub>	ns max
Feedthrough Error <sup>3</sup>	FT	- 1, 2, 3	15				Digital Inputs = V <sub>IL</sub> ; V <sub>REF</sub> = $\pm$ 10V; 100kHz Sinewave	$\pm$ mV p-p max
Reference Input Resistance R <sub>IN</sub>	R <sub>IN</sub>	- 1, 2, 3	5	5	5			k $\Omega$ min
			20	20	20			k $\Omega$ max
Input High Voltage V <sub>IH</sub>	V <sub>IH</sub>	- 1, 2, 3	2.4	2.4	2.4			V min
Input Low Voltage V <sub>IL</sub>	V <sub>IL</sub>	- 1, 2, 3	0.8	0.8	0.8			V max
Input Leakage Current I <sub>IN</sub>	I <sub>IN</sub>	- 1, 2, 3	1	1	1		V <sub>IN</sub> = 0V or V <sub>DD</sub>	$\pm$ $\mu$ A max
Input Capacitance C <sub>IN</sub>	C <sub>IN</sub>	- 1, 2, 3	5					pF max
Output Capacitance Pin 1 C <sub>OUT1</sub>	C <sub>OUT1</sub>	- 1, 2, 3	100				Digital Input = V <sub>IH</sub>	pF max
Pin 2 C <sub>OUT2</sub>	C <sub>OUT2</sub>	- 1, 2, 3	35				Digital Input = V <sub>IH</sub>	pF max
Pin 1 C <sub>OUT1</sub>	C <sub>OUT1</sub>	- 1, 2, 3	35				Digital Input = V <sub>IL</sub>	pF max
Supply Current I <sub>DD</sub>	I <sub>DD</sub>	- 1, 2, 3	2	2	2		Digital Inputs = V <sub>IL</sub> or V <sub>IH</sub>	mA max

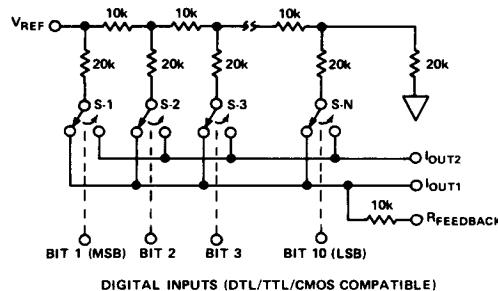
NOTES

<sup>1</sup>V<sub>DD</sub> = + 15V; V<sub>OUT1</sub> = V<sub>OUT2</sub> = 0V; V<sub>REF</sub> = + 10V unless otherwise stated.

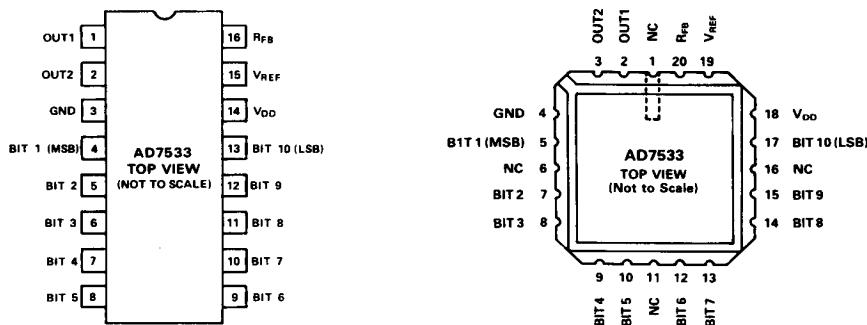
<sup>2</sup>Measured using internal feedback resistor and includes effect of leakage current and gain TC.

<sup>3</sup>Feedthrough error can be reduced by connecting the lid of the ceramic package to ground.

### 3.2.1 Functional Block Diagram and Terminal Assignments.



DIGITAL INPUTS (DTL/TTL/CMOS COMPATIBLE)



### 3.2.4 Microcircuit Technology Group.

This microcircuit is covered by technology group (80).

### 4.2.1 Life Test/Burn-In Circuit.

Steady state life test is per MIL-STD-883 Method 1005. Burn-in is per MIL-STD-883 Method 1015 test condition (B).

